

Single Phase Glass Passivated Silicon Bridge Rectifier

$V_{RRM} = 600 \text{ V}$ -
 $I_O = 4 \text{ A}$

Features

- Plastic package has Underwriters Laboratory Flammability Classification 94V-0
- High case dielectric strength of 1500 V_{RMS}
- Glass passivated chip junction
- Ideal for printed circuit boards
- High surge overload rating
- High temperature soldering guaranteed: 260°C/ 10 seconds, 0.375 (9.5mm) lead length
- Not ESD Sensitive

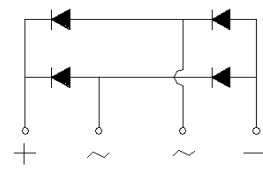
Mechanical Data

Case: Molded plastic body over passivated junctions

Terminals: Plated leads, solderable per MIL-STD-750 Method 2026.

Mounting position: Any

GBU Package



Maximum ratings at $T_c = 25 \text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	GBU4J	GBU4K	GBU4M
Repetitive peak reverse voltage	V_{RRM}		600	800	1000
RMS reverse voltage	V_{RMS}		420	560	700
DC blocking voltage	V_{DC}		600	800	1000
Operating temperature	T_j		-55 to 150	-55 to 150	-55 to 150
Storage temperature	T_{stg}		-55 to 150	-55 to 150	-55 to 150

Electrical characteristics at $T_c = 25 \text{ }^{\circ}\text{C}$, unless otherwise specified

Single phase, half sine wave, 60 Hz, resistive or inductive load.

For capacitive load derate current by 20%.

Parameter	Symbol	Conditions	GBU4J	GBU4K	GBU4M
Maximum average forward rectified current ^{1,2}	I_O	$T_c = 100 \text{ }^{\circ}\text{C}$	4.0	4.0	4.0
Peak forward surge current	I_{FSM}	$t_p = 8.3 \text{ ms}$, half sine	150	150	150
Maximum instantaneous forward voltage drop per leg	V_F	$I_F = 4 \text{ A}$	1.1	1.1	1.1
Maximum DC reverse current at rated DC blocking voltage per leg	I_R	$T_a = 25 \text{ }^{\circ}\text{C}$ $T_a = 125 \text{ }^{\circ}\text{C}$	5 500	5 500	5 500
Rating for fusing	I^2t	$t < 8.3 \text{ ms}$	93	93	93
Typical junction capacitance per leg ³	C_j		45	45	45
Typical thermal resistance per leg ^{1,2}	$R_{\theta JA}$ $R_{\theta JL}$		22 4.2	22 4.2	22 4.2

¹ - Device mounted on 40 mm x 40 mm x 1.5 mm Al plate heatsink

² - Recommended mounted position is to bolt down device on a heatsink with silicon thermal compound for maximum heat transfer using #6 screw.

³ - Measured at 1.0 MHz and applied reverse bias of 4.0 V



1000 V



Unit

V

V

V

°C

°C

Unit

A

A

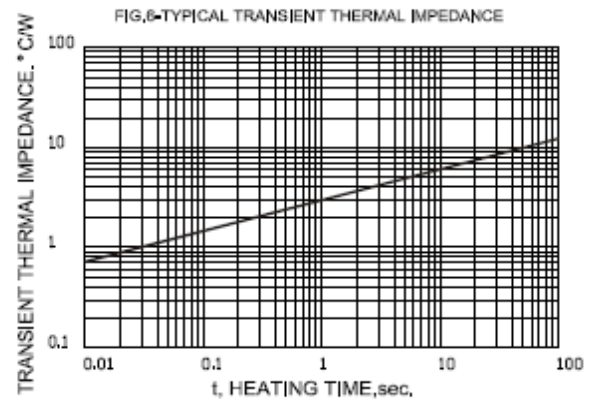
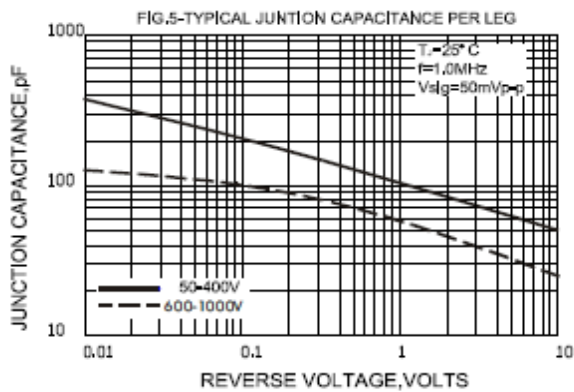
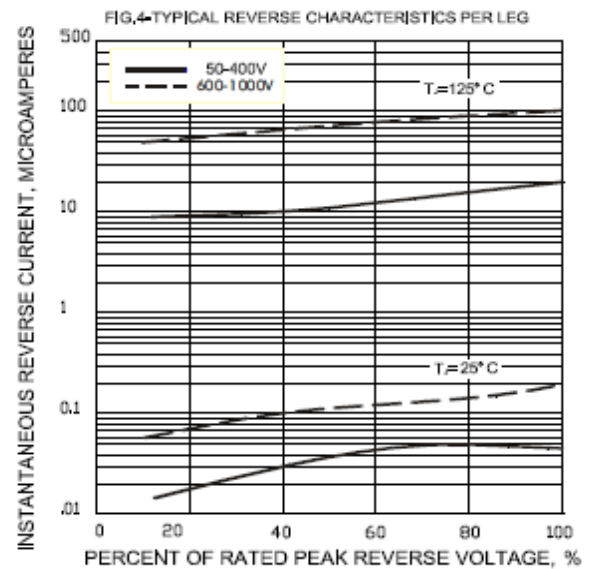
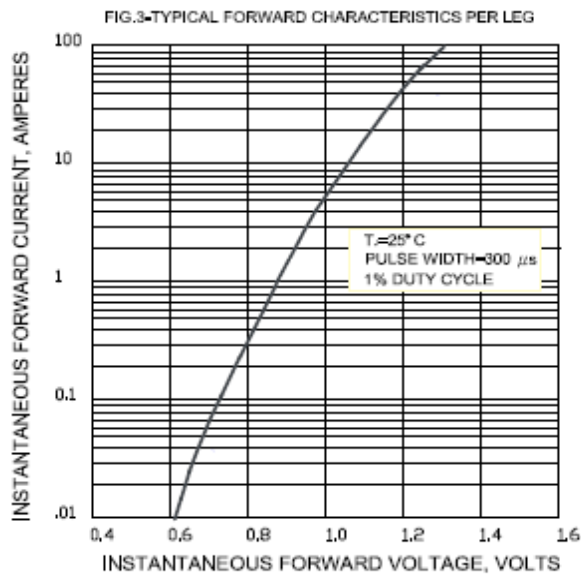
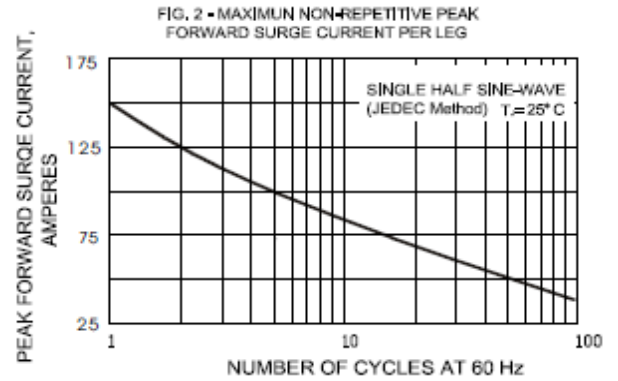
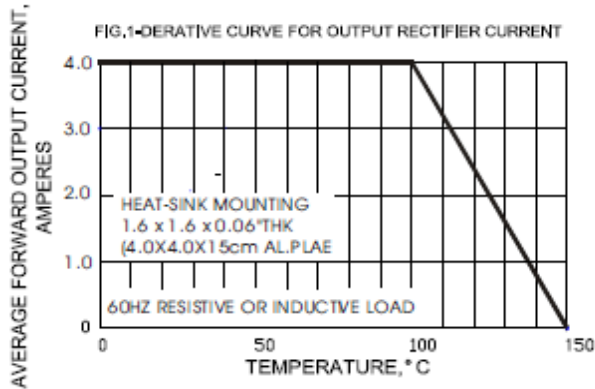
V

μA

A²sec

pF

°C/W

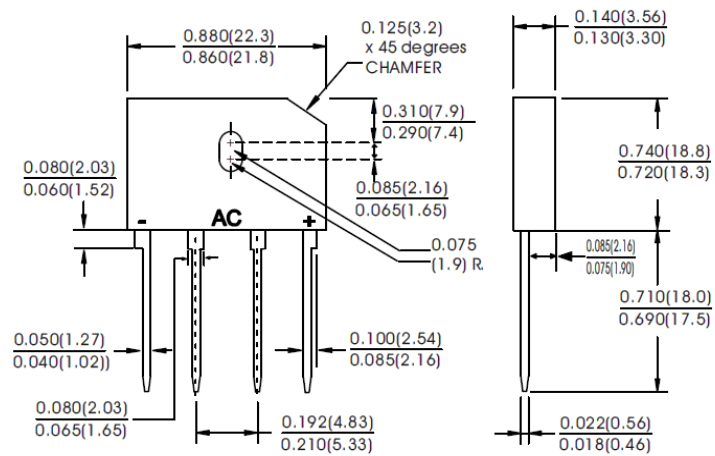




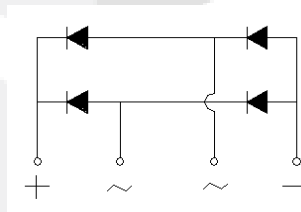
Package dimensions and terminal configuration

Product is marked with part number and terminal configuration.

GBU



Dimensions in inches and (millimeters)





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